

Amendment To The Claims

1. (Currently Amended) A semiconductor device comprising:
a semiconductor base;
a first insulation film which is provided on said semiconductor base and is made of a silicon material;
a second insulation film which is provided on said first insulation film, is made of an organic material, and is thicker than said first insulation film;
a third insulation film which is provided on said second insulation film, is made of a silicon material, and is thinner than said second insulation film; and
~~a wiring layer which is provided on said third insulation film~~ a metal layer which is grown on a seed layer which is provided on said third insulation film, and forms a wiring layer with said seed layer, wherein a current flows between said wiring layer and an external terminal.
2. (Original) The semiconductor device according to claim 2, further comprising
a fourth insulation film which is provided between said third insulation film and said wiring layer so as to cover an entire surface of said third insulation film, and is made of an organic material.
3. (Original) The semiconductor device according to claim 2, further comprising
a fifth insulation film which is provided between said fourth insulation film and said wiring layer and is made of a silicon material.
4. (Original) The semiconductor device according to claim 3,
wherein said fifth insulation film has a top view shape same as that of said wiring layer.
5. (Original) The semiconductor device according to claim 2,
wherein said forth insulation film is made of polybenzoxazole resin.
6. (Original) The semiconductor device according to claim 1,
wherein said wiring layer is made of metal.

7. (Original) The semiconductor device of claim 6,
wherein said wiring layer constitutes a metal pad which is connected to said external terminal, and/or a metal wire through which the current flows via said metal pad

Claims 8-13 (Withdrawn)

14. (Currently Amended) A semiconductor device comprising:
a semiconductor base;
a first insulation film which is provided on said semiconductor base;
a second insulation film which is provided on said first insulation film and is thicker than said first insulation film;
a third insulation film which is provided on said second insulation film and is made of a material having a moisture resistant property; and
~~a wiring layer which is provided on said third insulation film~~ a metal layer which is grown on a seed layer which is provided on said third insulation film, and forms a wiring layer with said seed layer, wherein a current flows between said wiring layer and an external terminal.

15. (Original) The semiconductor device according to claim 14, further comprising
a fourth insulation film which is provided between said third insulation film and said wiring layer so as to cover an entire surface of said third insulation film in order to prevent said third insulation film from being damaged.

16. (Original) The semiconductor device according to claim 15, further comprising
a fifth insulation film which is provided between said fourth insulation film and said wiring layer to function as an adhesive layer for preventing separation of said wiring layer.

17. (Original) The semiconductor device according to claim 16,
wherein said fifth insulation film has a top view shape same as that of said wiring layer.

18. (Original) The semiconductor device according to claim 15, wherein said fourth insulation film functions as an adhesive layer for preventing separation of said wiring layer.

19. (Original) The semiconductor device according to claim 18, wherein said fourth insulation film is made of polybenzoxazole resin.

20. (Original) The semiconductor device according to claim 14, wherein said wiring layer is made of metal.

21. (Original) The semiconductor device according to claim 20, wherein said wiring layer constitutes a metal pad which is connected to said external terminal, and/or a metal wire through which the current flows via a metal pad.

Claims 22-28 (Withdrawn)

29. (New) A semiconductor device comprising:
a semiconductor base;
a first insulation film which is provided on said semiconductor base and is made of a silicon material;
a second insulation film which is provided on said first insulation film, is made of an organic material, and is thicker than said first insulation film;
a third insulation film which is provided on said second insulation film, is made of an adhesive silicon material, and is thinner than said second insulation film; and
a wiring layer which is provided on said third insulation film, being prevented from separation over an entire region of the semiconductor device by an adhesion of said third insulation film which is sandwiched between said wiring layer and said second insulation film, wherein a current flows between said wiring layer and an external terminal.

30. (New) A semiconductor device comprising:

- a semiconductor base;
- a first insulation film which is provided on said semiconductor base and is made of a silicon material;
- a second insulation film which is provided on said first insulation film, is made of an organic material, and is thicker than said first insulation film;
- a third insulation film which is provided on said second insulation film, is made of silicon material, and is thinner than said second insulation film; and
- a metal layer which is patterned to form a wiring layer on said third insulation film, wherein a current flows between said wiring layers and an external terminal, said third insulation film having sufficient remaining thickness left by the patterning of said metal layer for covering substantially an entire surface of said second insulation film, containing the surface corresponding to the areas on which said wiring layer is provided.